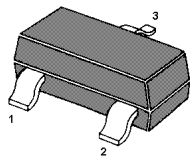
MMBTA14

NPN Silicon Epitaxial Planar Transistors

for general purpose applications, darlington transistor.

The transistor is subdivided into one group according to its DC current gain.
On special request, these transistors can be manufactured in different pin configurations.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a=25 °C)

	Symbol	Value	Unit
Collector Emitter Voltage	V_{CES}	30	V
Collector Base Voltage	V_{CBO}	30	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to +150	°C

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Max.	Unit
DC Current Gain at V_{CE}=5V, I_C=10mA at V_{CE}=5V, I_C=100mA	 h_{FE} h_{FE}	 10000 20000	 - -	 - -
Collector Emitter Breakdown Voltage at I_C=100µA	$V_{(BR)CES}$	30	-	V
Collector Cutoff Current at V_{CB}=30V	I_{CBO}	-	100	nA
Emitter Cutoff Current at V_{EB}=10V	I_{EBO}	-	100	nA
Collector Emitter Saturation Voltage at I_C=100mA, I_B=0.1mA	$V_{CE\ (sat)}$	-	1.5	V
Base Emitter On Voltage at I_C=100mA, V_{CE}=5V	$V_{BE(on)}$	-	2	V
Current Gain Bandwidth Product at V_{CE}=5V, I_C=10mA, f=100MHz	f_T	125	-	MHz